SIEMENS

IL215AT/216AT/217AT

PHOTOTRANSISTOR SMALL OUTLINE SURFACE MOUNT OPTOCOUPLER

FEATURES

- **High Current Transfer Ratio, I_F=1 mA**
  IL215AT, 20% Minimum
  IL216AT, 50% Minimum
  IL217AT, 100% Minimum
- **Isolation Voltage, 2500 VAC_{RMS}**
- **Electrical Specifications Similar to Standard 6 Pin Coupler**
- **Industry Standard SOIC-8 Surface Mountable Package**
- **Standard Lead Spacing, .05"**
- **Available in Tape and Reel (suffix T) (Conforms to EIA Standard RS481A)**
- **Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering**
- **Underwriters Lab File #E52744 (Code Letter P)**

DESCRIPTION

The IL215AT/216AT/217AT is an optically coupled pair with a Gallium Arsenide infrared LED and a silicon NPN phototransistor. Signal information, including a DC level, can be transmitted by the device while maintaining a high degree of electrical isolation between input and output. The IL215AT/216AT/217AT comes in a standard SOIC-8 small outline package for surface mounting which makes it ideally suited for high density applications with limited space. In addition to eliminating through-holes requirements, this package conforms to standards for surface mounted devices.

The high CTR at low input current is designed for low power consumption requirements such as CMOS microprocessor interfaces.

Maximum Ratings

Emitter

Peak Reverse Voltage ..... 6.0 V
Continuous Forward Current ..... 60 mA
Power Dissipation at 25°C ..... 90 mW
Derate Linearly from 25°C ..... 1.2 mW/°C

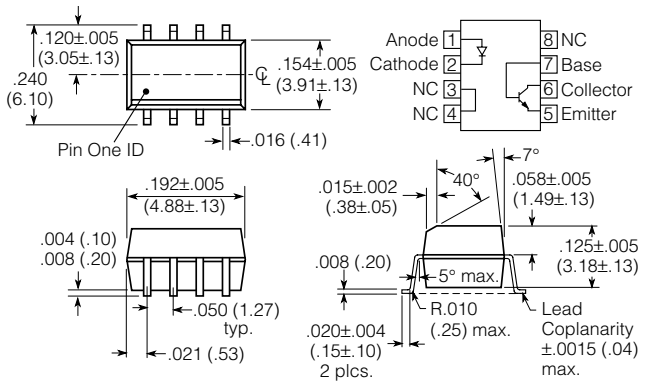
Detector

Collector-Emitter Breakdown Voltage ..... 30 V
Emitter-Collector Breakdown Voltage ..... 7 V
Collector-Base Breakdown Voltage ..... 70 V
Power Dissipation ..... 150 mW
Derate Linearly from 25°C ..... 2.0 mW/°C

Package

Total Package Dissipation at 25°C Ambient (LED + Detector) ..... 280 mW
Derate Linearly from 25°C ..... 3.3 mW/°C
Storage Temperature ..... –55°C to +150°C
Operating Temperature ..... –55°C to +100°C
Soldering Time at 260°C ..... 10 sec.

Package Dimensions in Inches (mm)



TOLERANCE: ±.005 (unless otherwise noted)

Characteristics (T_A=25°C)

	Symbol	Min.	Typ.	Max.	Unit	Condition
Emitter						
Forward Voltage	V_F		1.0	1.5	V	I_F=1 mA
Reverse Current	I_R		0.1	100	µA	V_R=6.0 V
Capacitance	C_O		25		pF	V_R=0
Detector						
Breakdown Voltage						
Collector-Emitter	BV_{CEO}	30			V	I_C=10 µA
Emitter-Collector	BV_{ECO}	7			V	I_E=10 µA
Collector-Emitter						V_{CE}=10 V,
Dark Current	$I_{CEOdark}$		5	50	nA	I_F =0
Collector-Emitter						
Capacitance	C_{CE}		10		pF	V_{CE}=0
Package						
DC Current Transfer	CTR_{DC}				%	I_F=1 mA, V_{CE}=5 V
IL215AT		20	50			
IL216AT		50	80			
IL217AT		100	130			
Collector-Emitter						I_C=0.1 mA,
Saturation Voltage	$V_{CE\,sat}$			0.4		I_F=1 mA
Isolation Test						
Voltage	V_{IO}	2500			VAC_{RMS}	
Capacitance,						
Input to Output	C_{IO}		0.5		pF	
Resistance,						
Input to Output	R_{IO}		100		GΩ	
Switching Time	t_{ON}, t_{OFF}		3.0		µs	I_C=2 mA, R_E=100 Ω, V_{CE}=10 V

Specifications subject to change.

Figure 1. Forward voltage versus forward current

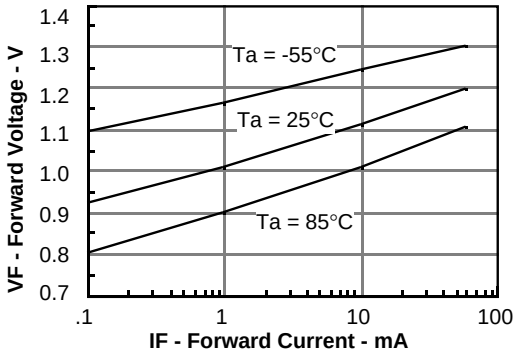


Figure 2. Normalized non-saturated and saturated CTRce versus LED current

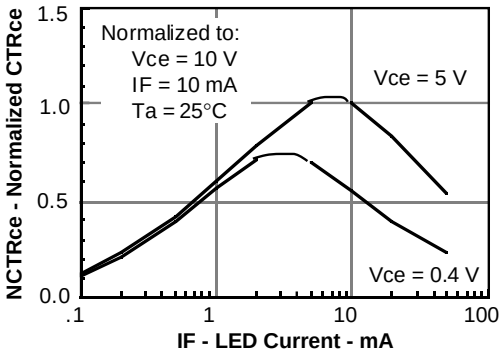


Figure 3. Collector-emitter current versus LED current

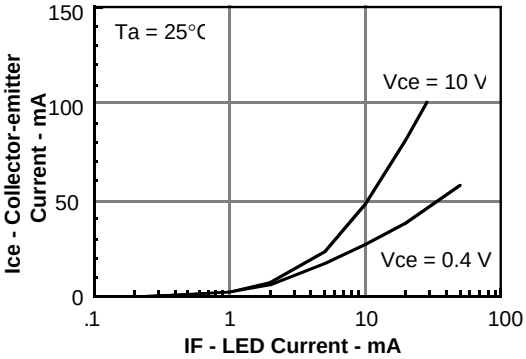


Figure 4. Normalized collector-base photocurrent versus LED current

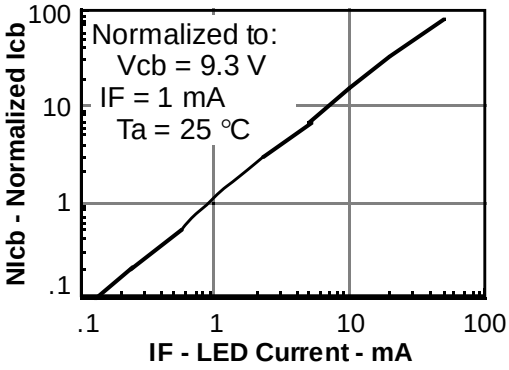


Figure 5. Collector-base photocurrent versus LED current

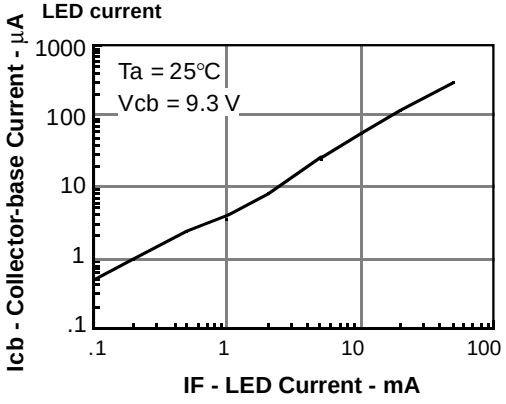


Figure 6. Collector-emitter leakage current versus temperature

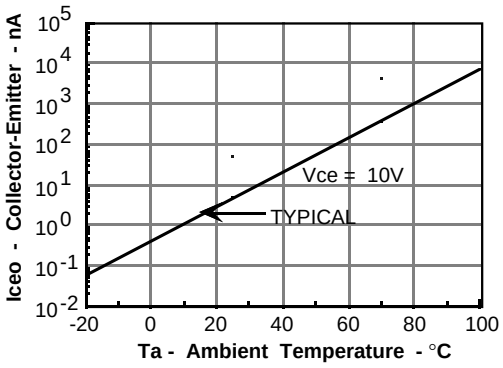


Figure 7. Normalized saturated HFE versus base current and temperature

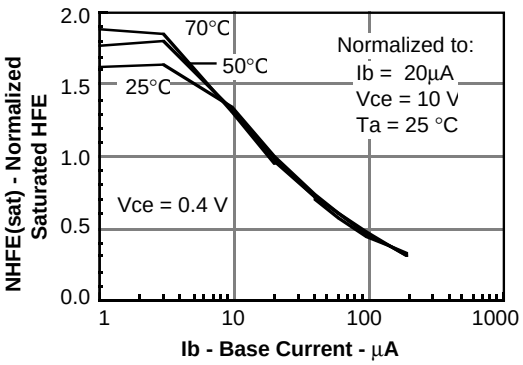


Figure 8. Normalized non-saturated and saturated CTRce versus LED current

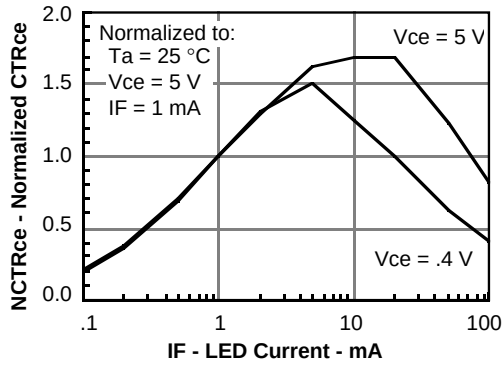


Figure 9. Normalized non-saturated and saturated collector-emitter current versus LED current

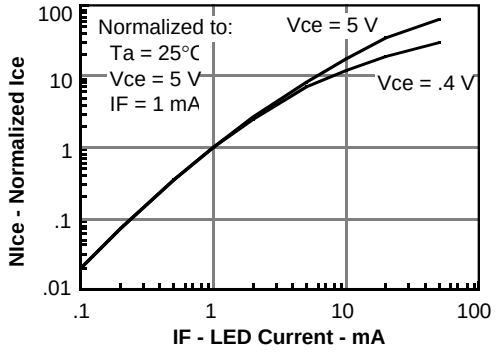


Figure 10. Normalized collector-base photocurrent versus LED current

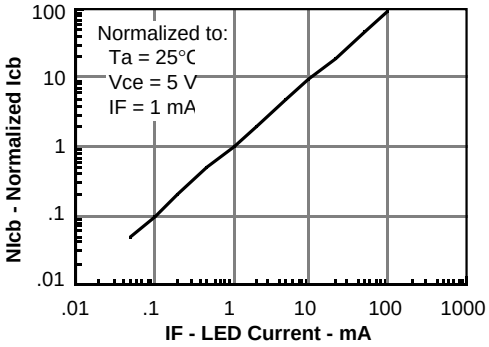


Figure 11. Collector-base photocurrent versus LED current

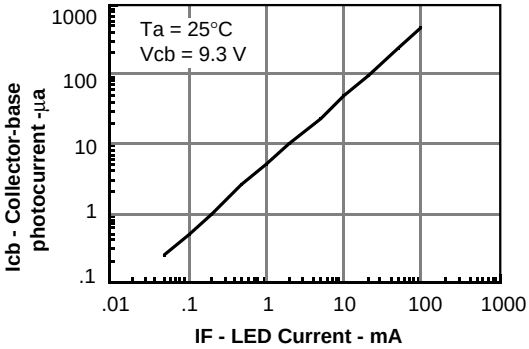


Figure 12. High to low propagation delay versus LED current and load resistor

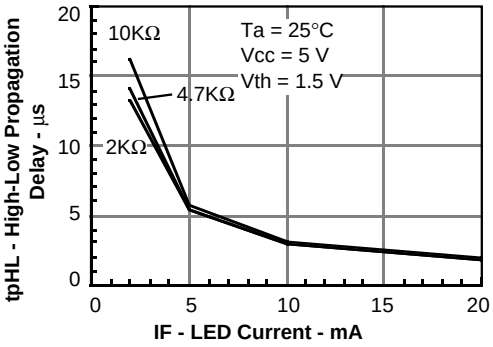


Figure 13. Low to high propagation delay versus LED current and load resistor

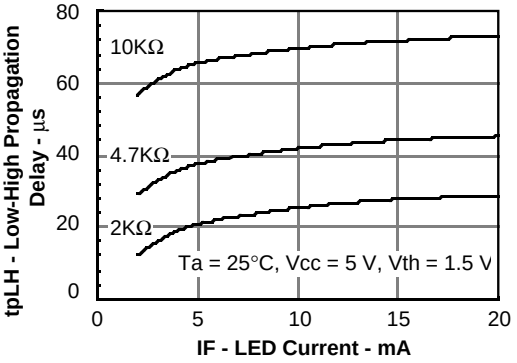


Figure 14. Normalized non-saturated HFE versus base current and temperature

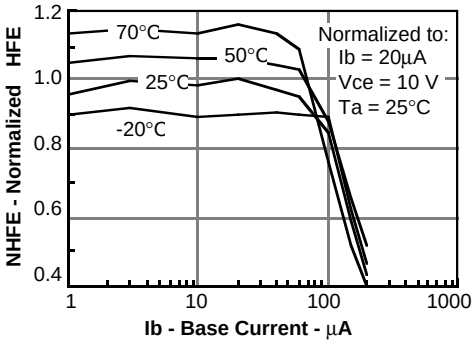


Figure 15. Typical switching characteristics versus base resistance (saturated operation)

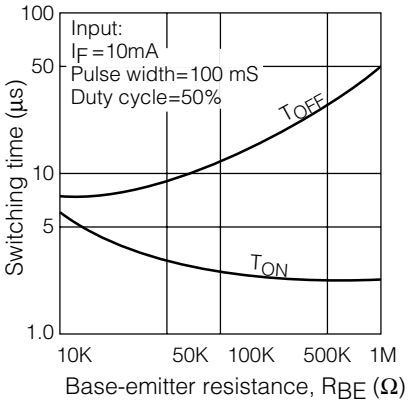


Figure 16. Typical switching times versus load resistance